

Surface Mount Schottky Barrier Rectifier

Reverse Voltage - 20 to 200 V

Forward Current - 2.0A

Features

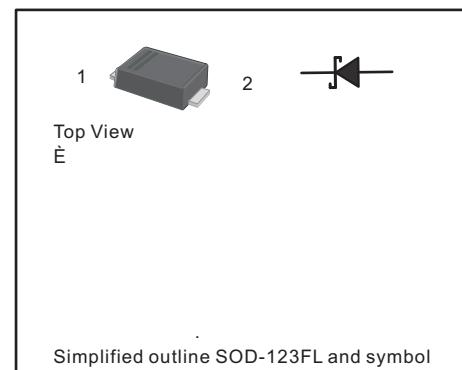
- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 15mg 0.00048oz

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	ÜS220S	ÜS240S	ÜS260S	ÜS280S	ÜS2100S	ÜS2120S	ÜS2150S	ÜS220FL	Units					
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V					
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	84	105	140	V					
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V					
Maximum Average Forward Rectified Current	I _{F(AV)}	2.0							A						
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	50							A						
Max Instantaneous Forward Voltage at 2A	V _F	0.55		0.70		0.85		0.95		V					
Maximum DC Reverse Current T _a = 25°C at Rated DC Reverse Voltage T _a = 100°C	I _R	0.5 5			0.3 3			mA							
Typical Junction Capacitance ⁽¹⁾	C _J	220		80											
Typical Thermal Resistance ⁽²⁾	R _{θJA}	85							°C/W						
Operating Junction Temperature Range	T _j	-55 ~ +125							°C						
Storage Temperature Range	T _{stg}	-55 ~ +150							°C						

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

